

BGD902

860 MHz, 18.5 dB gain power doubler amplifier Rev. 08 — 7 June 2007

Product data sheet

Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package operating with a supply voltage of 24 V.

1.2 Features

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability

1.3 Applications

■ CATV systems operating in the 40 MHz to 900 MHz frequency range.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	f = 50 MHz	18.2	18.5	18.8	dB
		f = 900 MHz	19	19.5	20	dB
I _{tot}	total current consumption (DC)		<u>[1]</u> 405	420	435	mA

^[1] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 35 V.

Pinning information 2.

Table 2. **Pinning**

Pin	Description	Simplified outline	Symbol
1	input		
2, 3	common	1 3 5 7 9	5
5	+V _B		$\frac{1}{2}$
7, 8	common		
9	output		2 3 7 8 sym095



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3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BGD902	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2\times6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{B}	supply voltage		-	30	V
Vi	RF input voltage		-	70	dBmV
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperatu	ıre	-20	+100	°C

5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 900 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω .

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	f = 50 MHz	18.2	18.5	18.8	dB
		f = 900 MHz	19	19.5	20	dB
SL	slope cable equivalent	f = 40 MHz to 900 MHz	0.4	0.9	1.4	dB
FL	flatness of frequency response	f = 40 MHz to 900 MHz	-	±0.15	±0.3	dB
s ₁₁	input return	f = 40 MHz to 80 MHz	21	23	-	dB
	losses	f = 80 MHz to 160 MHz	22	24	-	dB
		f = 160 MHz to 320 MHz	21	24	-	dB
		f = 320 MHz to 550 MHz	18	23	-	dB
		f = 550 MHz to 650 MHz	17	23	-	dB
		f = 650 MHz to 750 MHz	16	24	-	dB
		f = 750 MHz to 900 MHz	16	26	-	dB
S ₂₂	output return	f = 40 MHz to 80 MHz	25	32	-	dB
	losses	f = 80 MHz to 160 MHz	23	31	-	dB
		f = 160 MHz to 320 MHz	20	29	-	dB
		f = 320 MHz to 550 MHz	20	28	-	dB
		f = 550 MHz to 650 MHz	19	31	-	dB
		f = 650 MHz to 750 MHz	18	29	-	dB
		f = 750 MHz to 900 MHz	17	22	-	dB

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Table 5. Characteristics ... continued

Bandwidth 40 MHz to 900 MHz; $V_R = 24 \text{ V}$; $T_{mb} = 35 \,^{\circ}\text{C}$; $Z_S = Z_I = 75 \,\Omega$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
s ₂₁	phase response	f = 50 MHz		-45	-	+45	deg
СТВ	composite triple	49 chs flat; $V_0 = 47 \text{ dBmV}$; $f_m = 859.25 \text{ MHz}$		-	-68.5	-67	dB
	beat	77 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 547.25 \text{ MHz}$		-	-70	-68	dB
		110 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 745.25 \text{ MHz}$		-	-63.5	-62	dB
		129 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 859.25 \text{ MHz}$		-	-60	-58	dB
		110 chs; $f_m = 400 \text{ MHz}$; $V_o = 49 \text{ dBmV}$ at 550 MHz	<u>[1]</u>	-	-64	-62	dB
		129 chs; $f_m = 650 \text{ MHz}$; $V_o = 49.5 \text{ dBmV}$ at 860 MHz	[2]	-	-58.5	-56.5	dB
X _{mod}	cross modulation	49 chs flat; $V_0 = 47 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$		-	-66.5	-64	dB
		77 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$		-	-69.5	-67	dB
		110 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$		-	-66	-63.5	dB
		129 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$		-	-64.5	-62	dB
		110 chs; $f_m = 400 \text{ MHz}$; $V_o = 49 \text{ dBmV}$ at 550 MHz	<u>[1]</u>	-	-63	-60	dB
		129 chs; $f_m = 860 \text{ MHz}$; $V_o = 49.5 \text{ dBmV}$ at 860 MHz	[2]	-	-61	-58	dB
CSO	composite second order distortion	49 chs flat; $V_0 = 47 \text{ dBmV}$; $f_m = 860.5 \text{ MHz}$		-	-65	-62	dB
		77 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 548.5 \text{ MHz}$		-	-72	-67	dB
		110 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 746.5 \text{ MHz}$		-	-65	-60	dB
		129 chs flat; $V_0 = 44 \text{ dBmV}$; $f_m = 860.5 \text{ MHz}$		-	-61	-58	dB
		110 chs; $f_m = 250 \text{ MHz}$; $V_o = 49 \text{ dBmV}$ at 550 MHz	<u>[1]</u>	-	-67	-63	dB
		129 chs; $f_m = 250 \text{ MHz}$; $V_o = 49.5 \text{ dBmV}$ at 860 MHz	[2]	-	-62	-58	dB
IMD2	second order distortion		[3]	-	-80	-74	dB
			<u>[4]</u>	-	-83	-77	dB
			<u>[5]</u>	-	-84	-78	dB
Vo	output voltage	IMD = -60 dB	[6]	64.5	66	-	dBmV
			[7]	65.5	67	-	dBmV
			[8]	67.5	69	-	dBmV
		CTB compression = 1 dB; 129 chs flat; f = 859.25 MHz		48.5	49.5	-	dBmV
		CSO compression = 1 dB; 129 chs flat; f = 860.5 MHz		50	53	-	dBmV
F	noise figure	f = 50 MHz		-	4.5	5	dB
		f = 550 MHz		-	5	5.5	dB
		f = 750 MHz		-	5.5	6.5	dB
		f = 900 MHz		-	6.5	8	dB
I _{tot}	total current consumption (DC)		<u>[9]</u>	405	420	435	mA

^[1] Tilt = 9 dB (50 MHz to 550 MHz); tilt = 3.5 dB at -6 dB offset (550 MHz to 750 MHz).

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^[2] Tilt = 12.5 dB (50 MHz to 860 MHz).

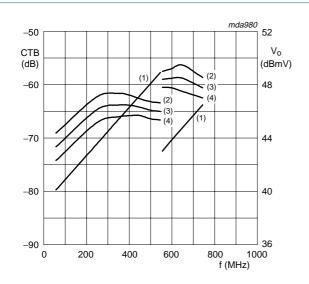
^[3] $f_p = 55.25 \text{ MHz}$; $V_p = 44 \text{ dBmV}$; $f_q = 805.25 \text{ MHz}$; $V_q = 44 \text{ dBmV}$; measured at $f_p + f_q = 860.5 \text{ MHz}$.

^[4] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 691.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 746.5$ MHz.

^[5] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz.

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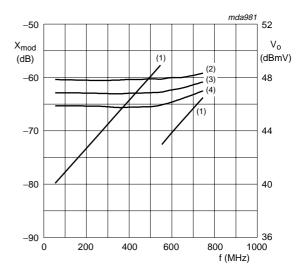
- [6] Measured according to DIN45004B: $f_p = 851.25$ MHz; $V_p = V_o$; $f_q = 858.25$ MHz; $V_q = V_o 6$ dB; $f_r = 860.25$ MHz; $V_r = V_o 6$ dB; measured at $f_p + f_q f_r = 849.25$ MHz.
- [7] Measured according to DIN45004B: $f_p = 740.25$ MHz; $V_p = V_o$; $f_q = 747.25$ MHz; $V_q = V_o 6$ dB; $f_r = 749.25$ MHz; $V_r = V_o 6$ dB; measured at $f_p + f_q f_r = 738.25$ MHz.
- [8] Measured according to DIN45004B: $f_p = 540.25$ MHz; $V_p = V_o$; $f_q = 547.25$ MHz; $V_q = V_o 6$ dB; $f_r = 549.25$ MHz; $V_r = V_o 6$ dB; measured at $f_p + f_q f_r = 538.25$ MHz.
- [9] The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 35 V.



 $Z_S=Z_L=75~\Omega;~V_B=24~V;~110~chs;~tilt=9~dB$ (50 MHz to 550 MHz); tilt= 3.5 dB at –6 dB offset (550 MHz to 750 MHz).

- (1) V_o.
- (2) Typ. +3 σ.
- (3) Typ.
- (4) Typ. -3σ .

Fig 1. Composite triple beat as a function of frequency under tilted conditions

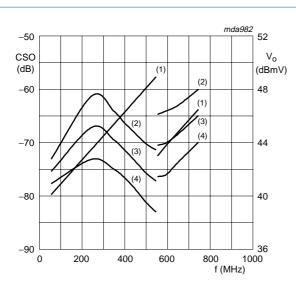


 $Z_S=Z_L=75~\Omega;~V_B=24~V;~110~chs;~tilt=9~dB$ (50 MHz to 550 MHz); tilt = 3.5 dB at -6~dB offset (550 MHz to 750 MHz).

- (1) V_o.
- (2) Typ. +3 σ.
- (3) Typ.
- (4) Typ. -3σ .

Fig 2. Cross modulation as a function of frequency under tilted conditions

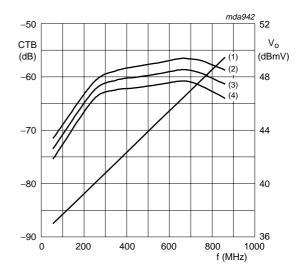
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 $Z_S=Z_L=75~\Omega;~V_B=24~V;~110~chs;~tilt=9~dB$ (50 MHz to 550 MHz); tilt= 3.5 dB at –6 dB offset (550 MHz to 750 MHz).

- (1) V_o.
- (2) Typ. +3 σ .
- (3) Typ.
- (4) Typ. –3 σ.

Fig 3. Composite second order distortion as a function of frequency under tilted conditions

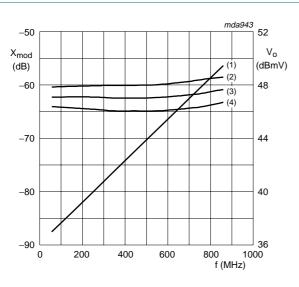


 Z_S = Z_L = 75 $\Omega;~V_B$ = 24 V; 129 chs; tilt = 12.5 dB (50 MHz to 860 MHz).

- (1) V_o.
- (2) Typ. +3 σ .
- (3) Typ.
- (4) Typ. -3σ .

Fig 4. Composite triple beat as a function of frequency under tilted conditions

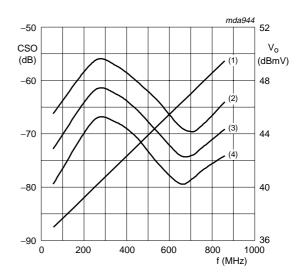
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 $Z_S = Z_L = 75~\Omega;~V_B = 24~V;~129~chs;~tilt = 12.5~dB$ (50 MHz to 860 MHz).

- (1) V_o.
- (2) Typ. +3 σ .
- (3) Typ.
- (4) Typ. -3σ .

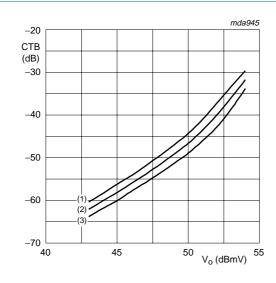
Fig 5. Cross modulation as a function of frequency under tilted conditions



 $Z_S = Z_L = 75~\Omega;~V_B = 24~V;~129~chs;~tilt = 12.5~dB$ (50 MHz to 860 MHz).

- (1) V_o.
- (2) Typ. $+3 \sigma$.
- (3) Typ.
- (4) Typ. -3σ .

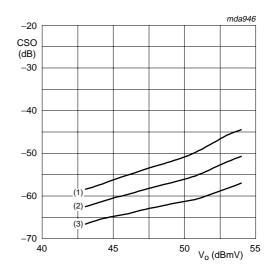
Fig 6. Composite second order distortion as a function of frequency under tilted conditions



 Z_S = Z_L = 75 Ω ; V_B = 24 V; 129 chs; f_m = 859.25 MHz.

- (1) Typ. $+3 \sigma$.
- (2) Typ.
- (3) Typ. -3 σ.

Fig 7. Composite triple beat as a function of output voltage



 $Z_S = Z_L = 75 \Omega$; $V_B = 24 V$; 129 chs; $f_m = 860.5 MHz$.

- (1) Typ. $+3 \sigma$.
- (2) Typ.
- (3) Typ. -3σ .

Fig 8. Composite second order distortion as a function of output voltage

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

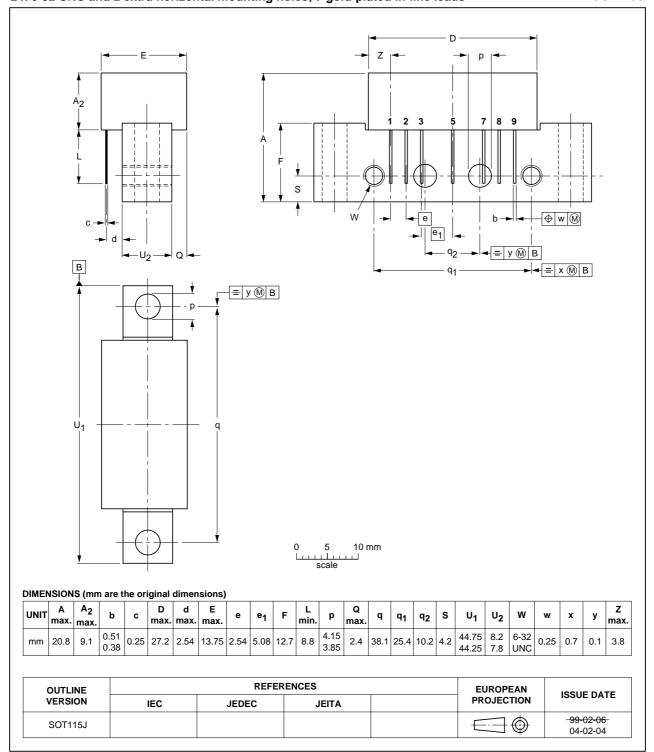


Fig 9. Package outline SOT115J

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7. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGD902_8	20070607	Product data sheet		BGD902_7
Modifications:	 The format of of NXP Sem 	of this data sheet has been re niconductors.	designed to comply wit	h the new identity guidelines
	 Legal texts h 	nave been adapted to the new	w company name wher	e appropriate.
	• Table 5 "Cha	aracteristics": updated values	of s ₁₁ and s ₂₂ .	
BGD902_7	20050308	Product data sheet		BGD902_902MI_6
BGD902_902MI_6	20011102	Product specification		BGD902_902MI_5
BGD902_902MI_5	19990329	Product specification		BGD902_N_3 and BGD902MI_N_1
BGD902_N_3	19980709	Preliminary specification		BGD902_N_2
BGD902_N_2	19980609	Preliminary specification		BGD902_1
BGD902_1	19980312	Preliminary specification		-
BGD902MI_N_1	19980831	Preliminary specification		-

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8. Legal information

8.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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